

## N-CHANNEL SILICON POWER MOSFET

## FAP-IIIB SERIES

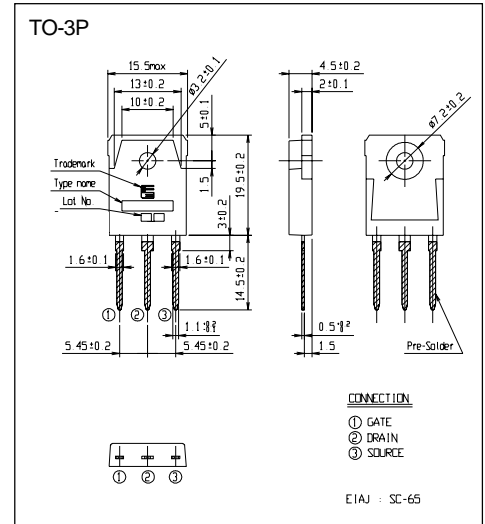
### ■ Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- High voltage
- Avalanche-proof

### ■ Applications

- Switching regulators
- DC-DC converters
- General purpose power amplifier

### ■ Outline Drawings



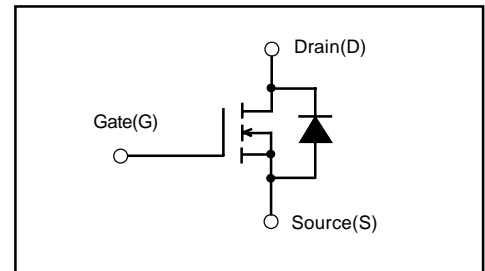
### ■ Maximum ratings and characteristics

#### ● Absolute maximum ratings (T<sub>c</sub>=25°C unless otherwise specified)

Item	Symbol	Rating	Unit	Remarks
Drain-source voltage	V <sub>DS</sub>	30	V	
Continuous drain current	I <sub>D</sub>	±100	A	
Pulsed drain current	I <sub>D</sub> [puls]	±400	A	
Gate-source peak voltage	V <sub>GS</sub>	±16	V	
Maximum avalanche energy	E <sub>AV</sub>	1555.6	mJ	*1
Maximum power dissipation	P <sub>D</sub>	125	W	
Operating and storage temperature range	T <sub>ch</sub>	+150	°C	
	T <sub>stg</sub>	-55 to +150	°C	

\*1 L=0.207mH, V<sub>CC</sub>=12V

### ■ Equivalent circuit schematic



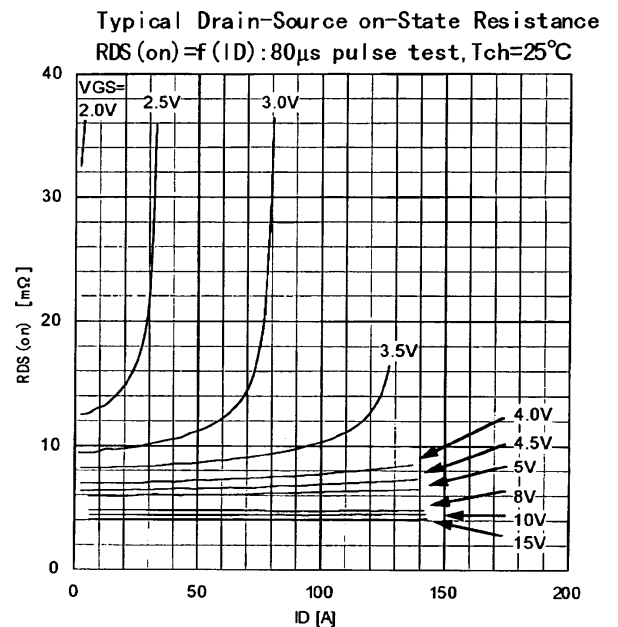
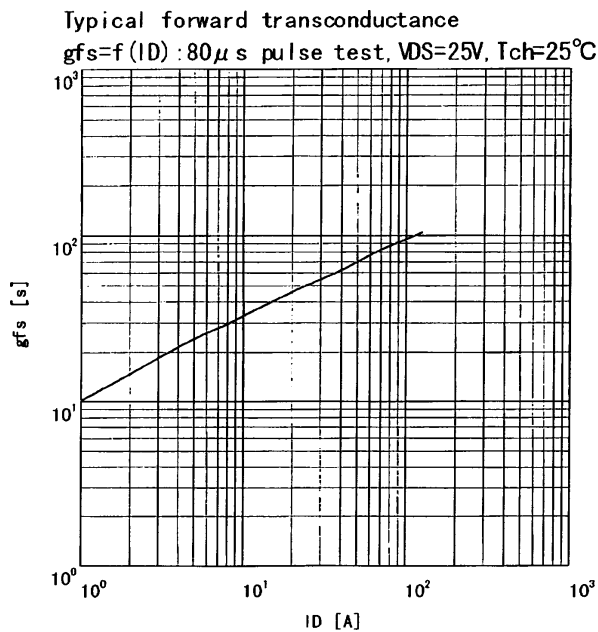
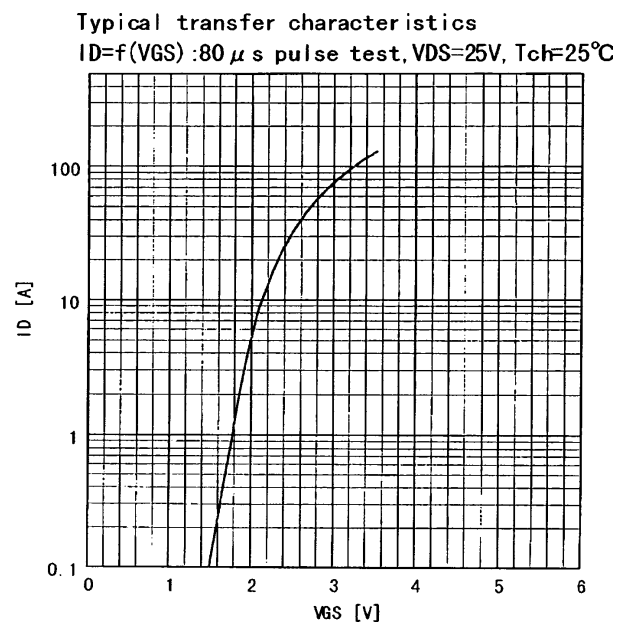
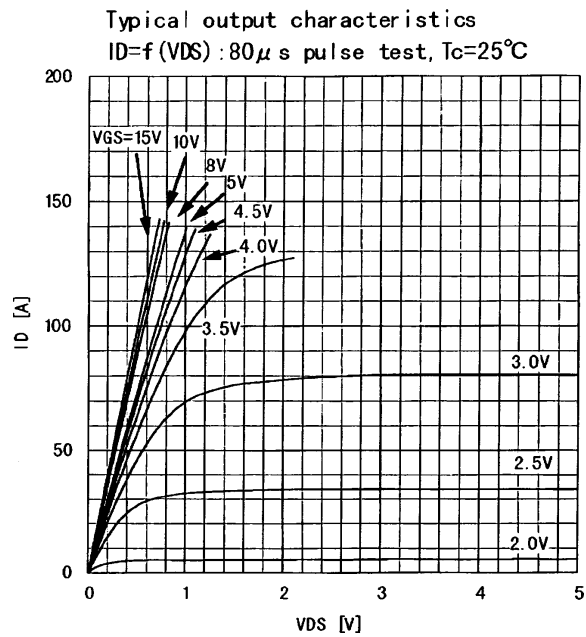
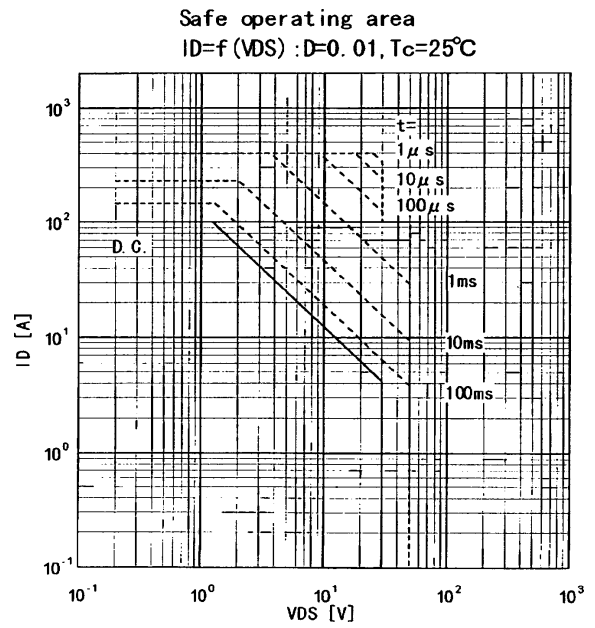
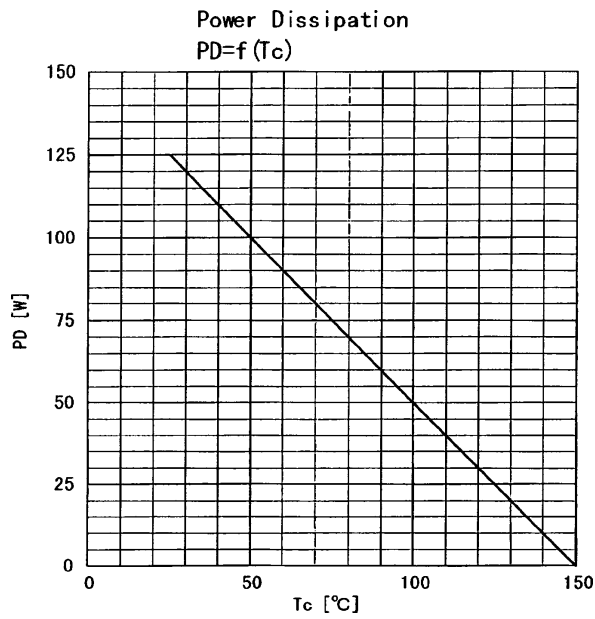
#### ● Electrical characteristics (T<sub>c</sub> =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA V <sub>GS</sub> =0V	30			V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =1mA V <sub>DS</sub> =V <sub>GS</sub>	1.0	1.5	2.0	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =30V V <sub>GS</sub> =0V	T <sub>ch</sub> =25°C	10	500	μA
			T <sub>ch</sub> =125°C	0.2	1.0	mA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V V <sub>DS</sub> =0V		10	100	nA
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =50A V <sub>GS</sub> =10V	V <sub>GS</sub> =4V	7.0	9.5	mΩ
			V <sub>GS</sub> =10V	4.5	5.5	mΩ
Forward transconductance	g <sub>fs</sub>	I <sub>D</sub> =50A V <sub>DS</sub> =25V	35	70		S
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1MHz		3900	5850	pF
Output capacitance	C <sub>oss</sub>			2000	3000	
Reverse transfer capacitance	C <sub>rss</sub>			850	1280	
Turn-on time	t <sub>d(on)</sub>	V <sub>CC</sub> =15V R <sub>G</sub> =10 Ω I <sub>D</sub> =100A V <sub>GS</sub> =10V		17	30	ns
	t <sub>r</sub>			70	110	
Turn-off time	t <sub>d(off)</sub>			250	380	
	t <sub>f</sub>			180	270	
Avalanche capability	I <sub>AV</sub>	L=100μH T <sub>ch</sub> =25°C	100			A
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =50A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1.0	1.5	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =50A		65		ns
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		0.12		μC

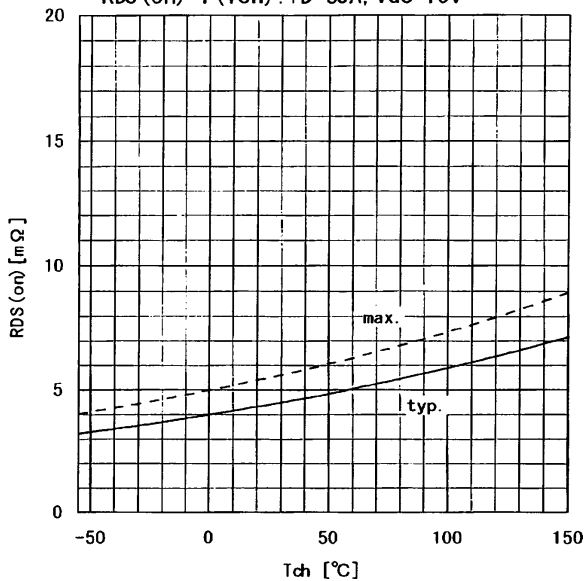
#### ● Thermal characteristics

Item	Symbol	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>			1.0	°C/W
	R <sub>th(ch-a)</sub>			35.0	°C/W

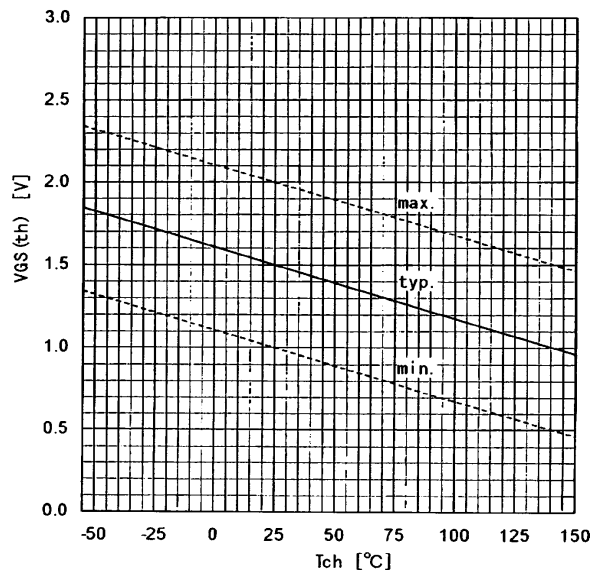
Characteristics



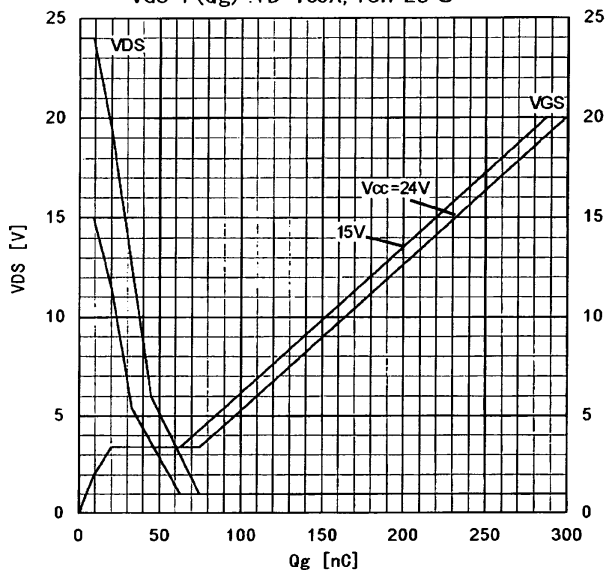
Drain-source on-state resistance  
 $R_{DS(on)} = f(T_{ch}) : I_D = 50A, V_{GS} = 10V$



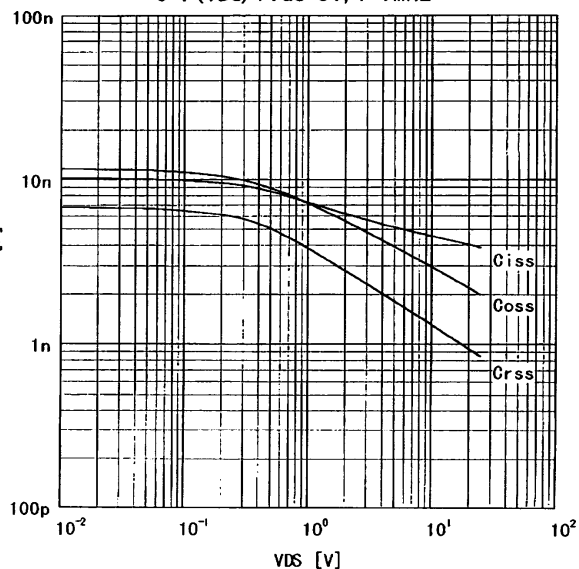
Gate Threshold Voltage vs. Tch  
 $V_{GS(th)} = f(T_{ch}) : V_{DS} = V_{GS}, I_D = 1mA$



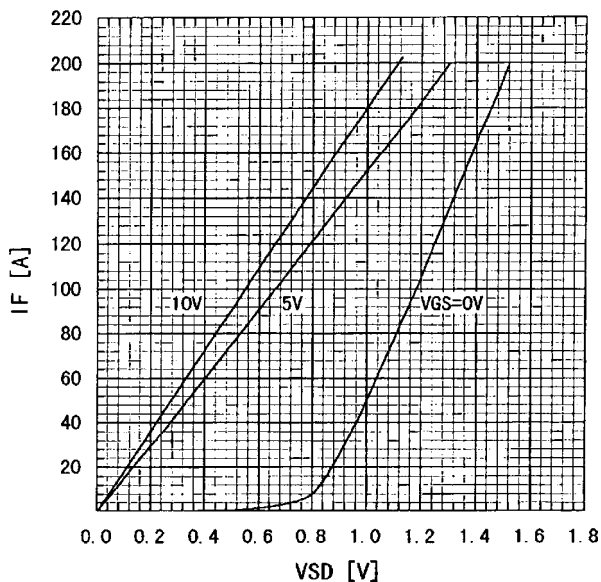
Typical Gate Charge Characteristics  
 $V_{GS} = f(Q_g) : I_D = 100A, T_{ch} = 25°C$



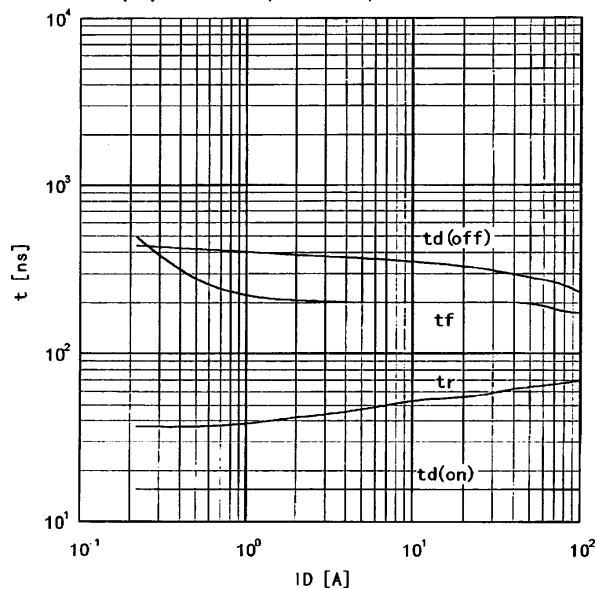
Typical capacitances  
 $C = f(V_{DS}) : V_{GS} = 0V, f = 1MHz$



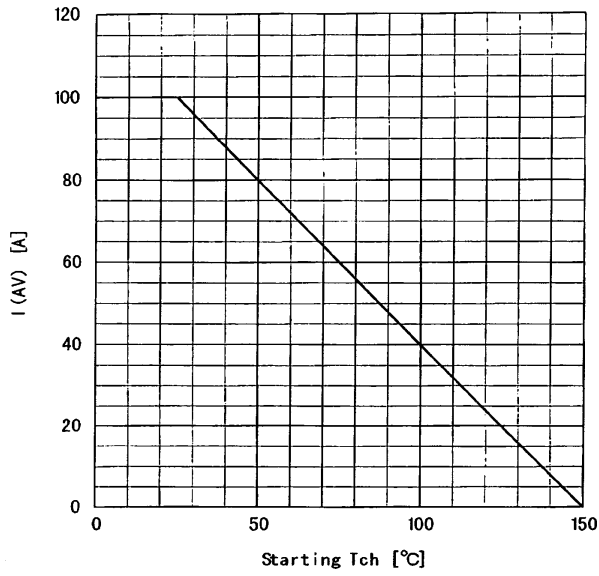
Typical Forward Characteristics of Reverse Diode  
 $I_F = f(V_{SD}) : 80\mu s \text{ pulse test}, T_{ch} = 25°C$



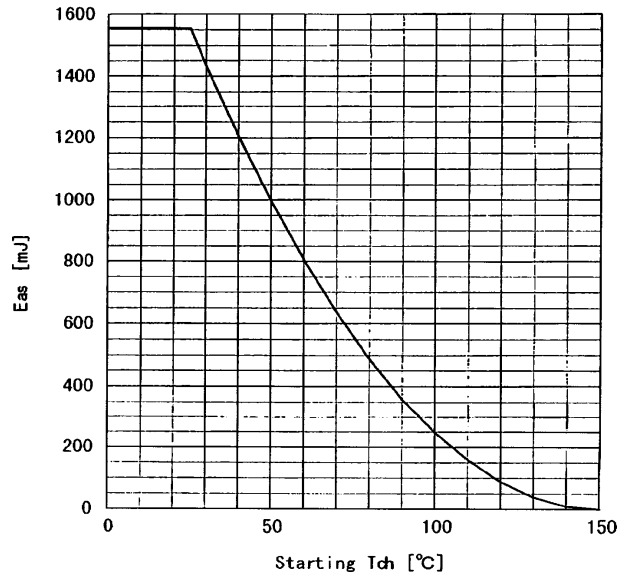
Typical Switching Characteristics vs. ID  
 $t = f(I_D) : V_{cc} = 15V, V_{GS} = 10V, R_G = 10\Omega$



Maximum Avalanche Current vs. starting T<sub>ch</sub>  
 $I_{AV} = f(\text{starting } T_{ch})$



Maximum Avalanche energy vs. starting T<sub>ch</sub>  
 $E_{as} = f(\text{starting } T_{ch}) : V_{CC} = 12V, I_{AV} \leq 100A$



Transient thermal impedande  
 $Z_{thch-c} = f(t)$  parameter:  $D = t/T$

